Li Wang

List of Publications by Year
in descending order

51 papers	1,083 citations	430754 18 h-index	434063 31 g-index
52 all docs	52 docs citations	52 times ranked	1475 citing authors

#	Article	IF	Citations
1	Co-substitution strategy to achieve a novel efficient deep-red-emitting SrKYTeO6:Mn4+ phosphor for plant cultivation lighting. Journal of Alloys and Compounds, 2022, 906, 164243.	2.8	15
2	Fluorescenceâ€enhanced Cs 4 PbBr 6 /CsPbBr 3 composites films synthesized by doubleâ€films solid phase reaction method. Luminescence, 2021, 36, 631-641.	1.5	4
3	A novel inequivalent double-site substituted red phosphor Li₄AlSbO₆:Mn⁴⁺ with high color purity: its structure, photoluminescence properties, and application in warm white LEDs. Journal of Materials Chemistry C, 2021, 9, 13236-13246.	2.7	28
4	Chemical unit co-substitution for a new far-red-emitting phosphor Ca3-6(NaLu)3LiSbO6:Mn4+ to achieve high quantum efficiency and superb thermal stability. Materials Today Advances, 2021, 12, 100193.	2.5	6
5	<i>In situ</i>tetrafluoroborate-modified MAPbBr₃nanocrystals showing high photoluminescence, stability and self-assembly behavior. Journal of Materials Chemistry C, 2020, 8, 1989-1997.	2.7	8
6	Perovskite MAPb(Br1â^'Cl)3 single crystals: Solution growth and electrical properties. Journal of Crystal Growth, 2020, 549, 125869.	0.7	7
7	Eco-Friendly Strategy To Improve Durability and Stability of Zwitterionic Capping Ligand Colloidal CsPbBr₃ Nanocrystals. Langmuir, 2020, 36, 6775-6781.	1.6	20
8	Photoflexoelectric effect in halide perovskites. Nature Materials, 2020, 19, 605-609.	13.3	132
9	Giant Stability Enhancement of CsPbX₃ Nanocrystal Films by Plasma-Induced Ligand Polymerization. ACS Applied Materials & Interfaces, 2019, 11, 35270-35276.	4.0	36
10	<i>In situ</i> inclusion of thiocyanate for highly luminescent and stable CH₃NH₃PbBr₃ perovskite nanocrystals. Nanoscale, 2019, 11, 1319-1325.	2.8	29
11	A new approach to stabilize the CsPbX3 quantum dots by double chemical coupling with stress. Journal of Alloys and Compounds, 2019, 782, 235-241.	2.8	7
12	Highly pure yellow light emission of perovskite CsPb(Br I)3 quantum dots and their application for yellow light-emitting diodes. Optical Materials, 2018, 80, 1-6.	1.7	17
13	Lithium and Silver Co-Doped Nickel Oxide Hole-Transporting Layer Boosting the Efficiency and Stability of Inverted Planar Perovskite Solar Cells. ACS Applied Materials & Interfaces, 2018, 10, 44501-44510.	4.0	73
14	Highly stable all-inorganic CsPbBr₃ nanocrystals film encapsulated with alumina by plasma-enhanced atomic layer deposition. Materials Express, 2018, 8, 469-474.	0.2	3
15	Epitaxial growth of InN thin films by plasma-enhanced atomic layer deposition. Journal of Applied Physics, 2018, 124, .	1.1	10
16	Fluorescence enhancement of Tb3+-doped CaAl-LDH by cytosine. Journal of Luminescence, 2018, 204, 42-50.	1.5	3
17	Low temperature growth of polycrystalline InN films on non-crystalline substrates by plasma-enhanced atomic layer deposition. Applied Surface Science, 2018, 459, 830-834.	3.1	13
18	Large flexoelectricity in Al2O3-doped Ba(Ti0.85Sn0.15)O3 ceramics. Applied Physics Letters, 2017, 110, .	1.5	25

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19	Carrier transport via V-shaped pits in InGaN/GaN MQW solar cells. Chinese Physics B, 2017, 26, 038104.	0.7	2
20	Study on the band alignment of GaN/CH3NH3PbBr3 heterojunction by x-ray photoelectron spectroscopy. Applied Physics Letters, 2017, 111, .	1.5	3
21	<i>a</i>-Axis GaN/AlN/AlGaN Coreâ€"Shell Heterojunction Microwires as Normally Off High Electron Mobility Transistors. ACS Applied Materials & Interfaces, 2017, 9, 41435-41442.	4.0	14
22	Reduction of the resistivity of Ag/p-GaN contact by progressive breakdown of the interfacial contamination layer. Journal of Applied Physics, 2015, 118, 165703.	1.1	4
23	Roles of V-shaped pits on the improvement of quantum efficiency in InGaN/GaN multiple quantum well light-emitting diodes. Journal of Applied Physics, 2014, 116, .	1.1	70
24	Crystallographic tilting of AlN/GaN layers on miscut Si (111) substrates. Materials Letters, 2014, 115, 89-91.	1.3	8
25	Influence of miscut angle of Si(111) substrates on the performance of InGaN LEDs. Applied Physics Express, 2014, 7, 012102.	1.1	3
26	Stress Distribution in GaN Films grown on Patterned Si (111) Substrates and Its Effect on LED Performance. Chinese Physics Letters, 2013, 30, 098101.	1.3	6
27	Effects of reflector-induced interferences on light extraction of InGaN/GaN vertical light emitting diodes. Journal of Luminescence, 2011, 131, 1836-1839.	1.5	4
28	Giant enhancement of top emission from ZnO thin film by nanopatterned Pt. Applied Physics Letters, 2009, 94, .	1.5	106
29	Photoluminescence of ZnO thin films grown on GaN templates by atmospheric pressure MOCVD. Journal of Luminescence, 2007, 122-123, 162-164.	1.5	17
30	The characteristics of GaN-based blue LED on Si substrate. Journal of Luminescence, 2007, 122-123, 185-187.	1.5	39
31	Study of polarization field in GaN-based blue LEDs on Si and sapphire substrate by electroluminescence. Journal of Luminescence, 2007, 122-123, 567-570.	1.5	14
32	The growth and properties of ZnO film on Si(111) substrate with an AlN buffer by AP-MOCVD. Journal of Luminescence, 2007, 122-123, 905-907.	1.5	18
33	Photoluminescence observations of hydrogen incorporation and outdiffusion in ZnO thin films. Journal of Luminescence, 2007, 124, 162-166.	1.5	6
34	The influence of the coating metals with various work function on the photoluminescence of a GaN-based blue LED wafer. Journal of Luminescence, 2007, 126, 636-640.	1.5	3
35	NH3-assisted growth approach for ZnO films by atmospheric pressure metal-organic chemical vapor deposition. Applied Physics A: Materials Science and Processing, 2007, 89, 645-650.	1.1	18
36	Properties of ZnO films grown on (0001) sapphire substrate using H2O and N2O as O precursors by atmospheric pressure MOCVD. Journal of Crystal Growth, 2006, 290, 426-430.	0.7	45

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37	Effect of the initial thin Ti buffer layers on the quality of ZnO thin films grown on Si(111) substrates by MOCVD. Superlattices and Microstructures, 2006, 40, 56-63.	1.4	16
38	Comparisons of structural and optical properties of ZnO films grown on (0001) sapphire and GaN/(0001) sapphire template by atmospheric-pressure MOCVD. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 127, 280-284.	1.7	12
39	Different properties of GaN-based LED grown on Si(111) and transferred onto new substrate. Science in China Series D: Earth Sciences, 2006, 49, 313-321.	0.9	19
40	Study of structural and luminescent properties of high-quality ZnO thin films treatment with hydrogen peroxide solution. Materials Science in Semiconductor Processing, 2005, 8, 569-575.	1.9	6
41	Structural and luminescent properties of ZnO epitaxial film grown on Si(111) substrate by atmospheric-pressure MOCVD. Journal of Crystal Growth, 2005, 275, 486-491.	0.7	28
42	High-quality ZnO films grown by atmospheric pressure metalâ€" organic chemical vapor deposition. Journal of Crystal Growth, 2005, 283, 87-92.	0.7	22
43	Atmospheric pressure MOCVD growth of high-quality ZnO films on GaN/Al2O3 templates. Journal of Crystal Growth, 2005, 283, 93-99.	0.7	42
44	Relationship between structure characteristic and blue luminescence in unintentional doped GaN layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 122, 72-75.	1.7	7
45	Influence of nitrogen annealing on structural and photoluminescent properties of ZnO thin film grown on c-Al2O3 by atmospheric pressure MOCVD. Materials Science in Semiconductor Processing, 2005, 8, 491-496.	1.9	11
46	Effect of high-temperature annealing on the structural and optical properties of ZnO films. Thin Solid Films, 2005, 491, 323-327.	0.8	39
47	Influence of hydrogen peroxide solution on the properties of ZnO thin films. Journal of Crystal Growth, 2004, 268, 71-75.	0.7	24
48	Study of the blue luminescence in unintentional doped GaN films grown by MOCVD. Journal of Luminescence, 2004, 106, 219-223.	1.5	16
49	The influence of Si-doping to the growth rate and yellow luminescence of GaN grown by MOCVD. Journal of Luminescence, 2001, 93, 321-326.	1.5	22
50	Growth of ZnO Films on Si(111) by Metalorganic Chemical Vapor Deposition with AlN and Low-Temperature ZnO Double Buffers. Advanced Materials Research, 0, 652-654, 594-598.	0.3	1
51	(CH3)2C=NHCH3PbBr3/CH3NH3PbBr3 Core-Shell Heterostruture Fabricated by In-Situ A-Site Reaction for Fast Response 1D Perovskite Photodetectors. Physical Chemistry Chemical Physics, 0, , .	1.3	1